

Silicon Diffused Power Transistor

BU2727AF

GENERAL DESCRIPTION

High voltage, high-speed switching npn transistor in a plastic full-pack envelope intended for use in horizontal deflection circuits of high resolution monitors. Designed to withstand V_{CES} pulses up to 1700V.

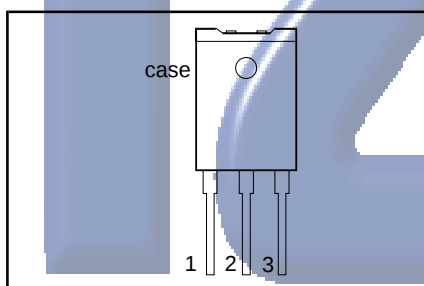
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1700	V
V_{CEO}	Collector-emitter voltage (open base)		-	825	V
I_C	Collector current (DC)		-	12	A
I_{CM}	Collector current peak value		-	30	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25\text{ }^{\circ}\text{C}$	-	45	W
V_{CESat}	Collector-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 0.91\text{ A}$	-	1.0	V
I_{Csat}	Collector saturation current	$f = 64\text{ kHz}$	5.0	-	A
t_s	Storage time	$I_{Csat} = 5.0\text{ A}; f = 64\text{ kHz}$	2.5	3.0	μs

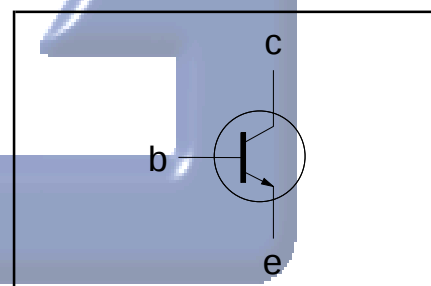
PINNING - SOT199

PIN	DESCRIPTION
1	base
2	collector
3	emitter
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1700	V
V_{CEO}	Collector-emitter voltage (open-base)		-	825	V
I_C	Collector current (DC)		-	12	A
I_{CM}	Collector current peak value		-	30	A
I_B	Base current (DC)		-	12	A
I_{BM}	Base current peak value		-	25	A
$-I_{B(AV)}$	Reverse base current	average over any 20 ms period	-	200	mA
$-I_{BM}$	Reverse base current peak value ¹		-	25	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25\text{ }^{\circ}\text{C}$	-	45	W
T_{stg}	Storage temperature		-65	150	$^{\circ}\text{C}$
T_J	Junction temperature		-	150	$^{\circ}\text{C}$

ESD LIMITING VALUES

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_C	Electrostatic discharge capacitor voltage	Human body model (250 pF, 1.5 k Ω)	-	10	kV

¹ Turn-off current.